

## CBRHD SERIES

**HIGH DENSITY SURFACE MOUNT  
½ AMP DUAL IN LINE  
BRIDGE RECTIFIER**

### FEATURES:

- Truly efficient use of board space, requires only 42mm<sup>2</sup> of board space vs. 120mm<sup>2</sup> of board space for industry standard 1.0 Amp surface mount bridge rectifier.
- 50% higher density (amps/mm<sup>2</sup>) than the industry standard 1.0 Amp surface mount bridge rectifier.
- Glass passivated chips for high reliability.

**HD<sup>TM</sup>  
BRIDGE**



**HDDIP CASE**

### DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRHD series types are silicon full wave bridge rectifiers mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

### MAXIMUM RATINGS: (T<sub>A</sub>=25°C unless otherwise noted)

	SYMBOL	CBRHD <b>-02</b>	CBRHD <b>-04</b>	CBRHD <b>-06</b>	CBRHD <b>-10*</b>	UNITS
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	200	400	600	1000	V
DC Blocking Voltage	V <sub>R</sub>	200	400	600	1000	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	140	280	420	700	V
Average Forward Current (T <sub>A</sub> =40°C)(1)	I <sub>O</sub>			0.5		A
Average Forward Current (T <sub>A</sub> =40°C)(2)	I <sub>O</sub>			0.8		A
Peak Forward Surge Current	I <sub>FSM</sub>			30		A
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>		-65 to +150			°C

### ELECTRICAL CHARACTERISTICS: (T<sub>A</sub>=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V <sub>F</sub>	I <sub>F</sub> =400mA (Per Diode)			1.0	V
I <sub>R</sub>	V <sub>R</sub> =Rated V <sub>RRM</sub>			5.0	μA
I <sub>R</sub>	V <sub>R</sub> =Rated V <sub>RRM</sub> , T <sub>A</sub> =125°C			500	μA
C <sub>J</sub>	V <sub>R</sub> =4.0V, f=1.0MHz		20		pF

(1) Mounted on a Glass-Epoxy P.C.B.

(2) Mounted on a Ceramic P.C.B.

\*Available on special order, please consult factory.

All dimensions in inches (mm).

### TOP VIEW

